

Taiwan Semiconductor

# 16A, 50V - 600V Super Fast Surface Mount Rectifier

#### **FEATURES**

- Low forward voltage drop
- Ideal for automated placement
- High current capability
- High surge current capability
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

#### **APPLICATIONS**

- DC to DC converter
- Switching mode converters and inverters
- Freewheeling application

#### **MECHANICAL DATA**

- Case: TO-263AB (D<sup>2</sup>PAK)
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.41g (approximately)

KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
I <sub>F</sub>	16	А		
V <sub>RRM</sub>	50 - 600	V		
I <sub>FSM</sub>	125	А		
T <sub>J MAX</sub>	150	°C		
Package	TO-263AB	(D <sup>2</sup> PAK)		
Configuration	Dual d	lies		

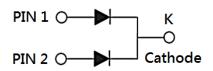








TO-263AB (D<sup>2</sup>PAK)



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)										
PARAMETER	SYMBOL	SFS 1601	SFS 1602	SFS 1603	SFS 1604	SFS 1605	SFS 1606	SFS 1607	SFS 1608	UNIT
		G	G	G	G	G	G	G	G	
Marking code on the device		SFS 1601G	SFS 1602G	SFS 1603G	SFS 1604G	SFS 1605G	SFS 1606G	SFS 1607G	SFS 1608G	
Repetitive peak reverse voltage	V <sub>RRM</sub>	50	100	150	200	300	400	500	600	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	35	70	105	140	210	280	350	420	V
Forward current	I <sub>F</sub>	16					А			
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>	125			A					
Junction temperature	$T_J$	-55 to +150			°C					
Storage temperature	T <sub>STG</sub>	-55 to +150			°C					



THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case thermal resistance	R <sub>eJC</sub>	2.5	°C/W

ELECTRICAL SPECIFICATIONS ( $T_A = 25^{\circ}C$ unless otherwise noted)						
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
Forward valtage per diada <sup>(1)</sup>	SFS1601G SFS1602G SFS1603G SFS1604G	I <sub>F</sub> = 8A, T <sub>J</sub> = 25°C	V <sub>F</sub>	-	0.975	V
Forward voltage per diode <sup>(1)</sup>	SFS1605G SFS1606G			-	1.300	V
	SFS1607G SFS1608G			-	1.700	V
Reverse current @ rated $V_R$ per diode <sup>(2)</sup>		$T_J = 25^{\circ}C$		-	10	μA
		T <sub>J</sub> = 125°C	I <sub>R</sub>	-	400	μA
Junction capacitance per diode SFS1602G SFS1602G SFS1603G SFS1604G SFS1605G SFS1606G SFS1607G SFS1608G		1MHz, V <sub>R</sub> = 4.0V	CJ	80	-	pF
				60	-	pF
Reverse recovery time		$I_F = 0.5A, I_R = 1.0A$ $I_{rr} = 0.25A$	t <sub>rr</sub>	-	35	ns

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION					
ORDERING CODE <sup>(1)</sup>	PACKAGE	PACKING			
SFS16xG	TO-263AB (D <sup>2</sup> PAK)	800 / Tape & Reel			

Notes:

1. "x" defines voltage from 50V(SFS1601G) to 600V(SFS1608G)



#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

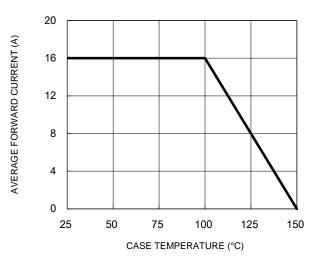


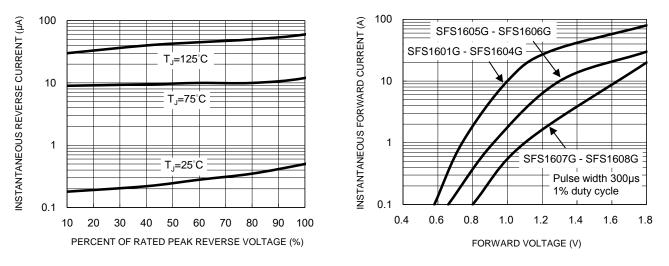
Fig.1 Forward Current Derating Curve

#### **Fig.3 Typical Reverse Characteristics**

100 90 SFS1601G - SFS1604G CAPACITANCE (pF) 80 SFS1605G - SFS1608G 70 60 50 f=1.0MHz Vsig=50mVp-p 40 1 10 100

**Fig.2 Typical Junction Capacitance** 

**Fig.4 Typical Forward Characteristics** 



### 150 PEAK FORWARD SURGE CURRENT (A) 8.3ms single half sine wave 125 100 75 50 25 0 10 100 1 NUMBER OF CYCLES AT 60 Hz

#### Fig.5 Maximum Non-Repetitive Forward Surge Current

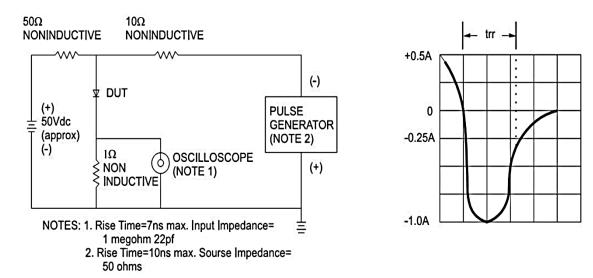
REVERSE VOLTAGE (V)

Version: O2103



### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 



#### Fig.6 Reverse Recovery Time Characteristic and Test Circuit Diagram

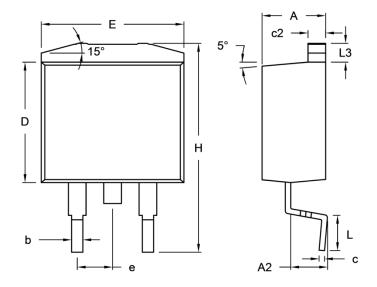


# SFS1601G - SFS1608G

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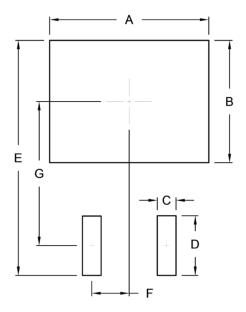
### PACKAGE OUTLINE DIMENSIONS

### TO-263AB (D<sup>2</sup>PAK)



DIM.	Unit	(mm)	Unit (	(inch)
	Min.	Max.	Min.	Max.
A	4.44	4.70	0.175	0.185
A2	2.03	2.79	0.080	0.110
b	0.68	0.94	0.027	0.037
с	0.36	0.53	0.014	0.021
c2	1.14	1.40	0.045	0.055
D	8.25	9.25	0.325	0.364
E	-	10.50	-	0.413
е	2.41	2.67	0.095	0.105
н	14.60	15.88	0.575	0.625
L	2.29	2.79	0.090	0.110
L3	1.14	1.40	0.045	0.055

### SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	10.80	0.425
В	8.30	0.327
С	1.27	0.050
D	4.05	0.159
E	15.95	0.628
F	2.54	0.100
G	9.775	0.385

#### **MARKING DIAGRAM**



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



# SFS1601G - SFS1608G

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